- **1N5711 AVAILABLE IN JANHC AND JANKC PER MIL-PRF-19500/444**
- **1N5712 AVAILABLE IN JANHC AND JANKC PER MIL-PRF-19500/445**
- **SCHOTTKY BARRIER DIODE CHIPS FOR GENERAL PURPOSE APPLICATION**
- **SILICON DIOXIDE PASSIVATED**
- **COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES, WITH THE EXCEPTION OF SOLDER REFLOW**

CD2810
CD5711
CD5712
CD6857
CD6858
CD6916

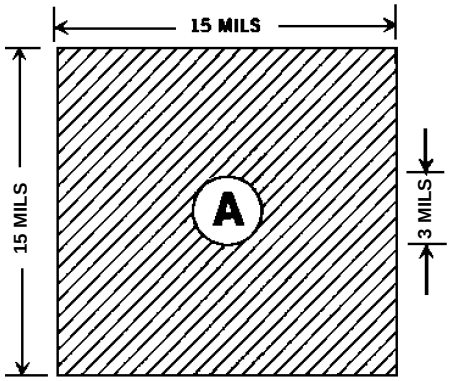
MAXIMUM RATINGS

Operating Temperature: -55°C to +125°C
Storage Temperature: -65°C to +150°C

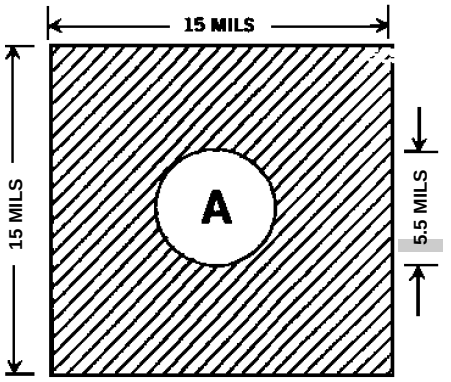
ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

CDI TYPE NUMBER	MINIMUM BREAKDOWN VOLTAGE (2)	MAXIMUM FORWARD VOLTAGE	MAXIMUM FORWARD VOLTAGE	MAXIMUM REVERSE LEAKAGE CURRENT		MAXIMUM CAPACITANCE @ V_R = 0 VOLTS f = 1.0 MHz	FIGURE NUMBER
	V_{BR} @ 10 μA	V_F @ 1 mA	V_F @ I_F	1_R @ V_R		C_T	
	VOLTS	VOLTS	VOLTS @ mA	nA	VOLTS	PICO FARADS	
CD2810	20	0.41	1.0 @ 35	100	15	1.2	1
CD5711	70	0.41	1.0 @15	200	50	2.0	2
CD5712	20	0.41	1.0 @ 35	150	16	1.2	1
CD6857	20	0.35	0.75 @ 35	150	16	4.5	2
CD6858	70	0.36	0.65 @ 15	200	50	4.5	2
CD6916	40 (2)	0.34	0.27 @ 0.1	100	1	5	2
			0.34 @ 1.0	200	20		
			0.47 @ 10.0	500	40		

NOTES: (1) Effective Minority Carrier Lifetime (τ) is 100 Pico Seconds
(2) CD6916 V_{BR} measured @ 500 nanoamps



BACKSIDE IS CATHODE
FIGURE 1



BACKSIDE IS CATHODE
FIGURE 2

DESIGN DATA

METALLIZATION:
Top: (Anode).....Al
Back: (Cathode)..... Au

AL THICKNESS.....25,000 Å Min

GOLD THICKNESS.....4,000 Å Min

CHIP THICKNESS..... .....10 Mils

TOLERANCES: ALL Dimensions ± 2 mils, Except Anode Pad Where Tolerance is ± 0.5 mils.

COMPENSATED DEVICES INCORPORATED
22 COREY STREET, MELROSE, MASSACHUSETTS 02176
PHONE (781) 665-1071 FAX (781) 665-7379
WEBSITE: http://www.cdi-diodes.com E-mail: mail@cdi-diodes.com

CD2810, CD5711, CD5712, CD6857, CD6858 and CD6916

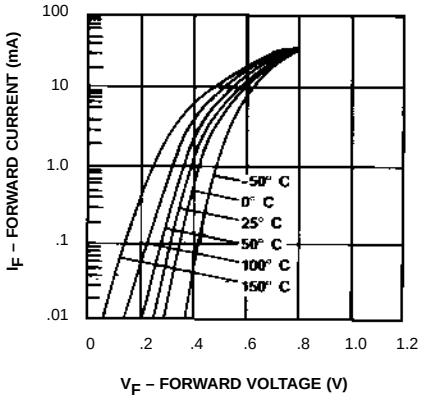


Figure 1.
I-V Curve Showing Typical Forward Voltage Variation with Temperature for the CD5712 and CD2810 Schottky Diodes.

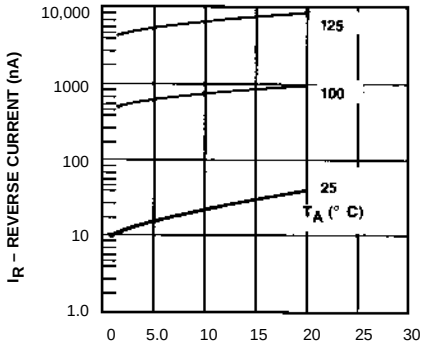


Figure 2.
CD5712 and CD2810
Typical Variation of Reverse Current (I_R) vs. Reverse Voltage (V_R) at Various Temperatures.

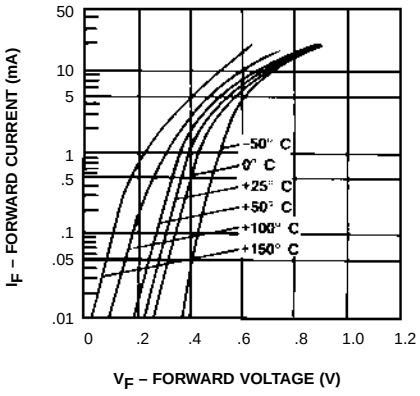


Figure 3.
I-V Curve Showing Typical Forward Voltage Variation with Temperature for Schottky Diode CD5711.

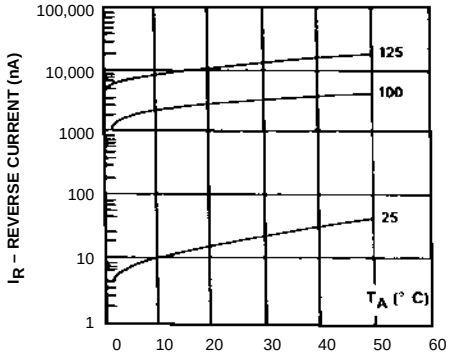


Figure 4.
CD5711 Typical Variation of Reverse Current (I_R) vs. Reverse Voltage (V_R) at Various Temperatures.

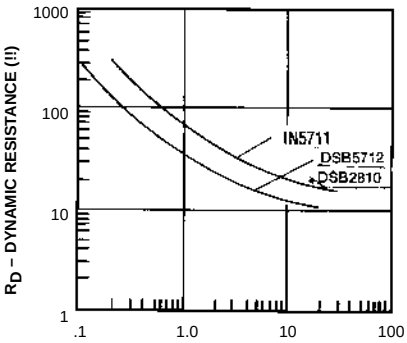


Figure 5.
Typical DynamiC Resistance (R_D) vs. Forward Current (I_F).